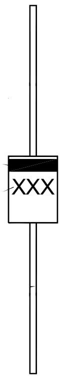
SILICON SCHOTTKY BARRIER DIODE

Glass Case DO-35

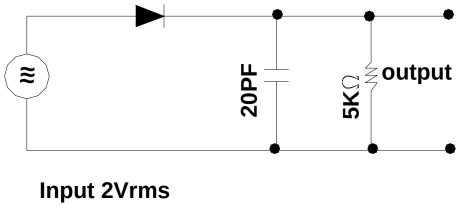


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_S	- 55 to + 175	°C

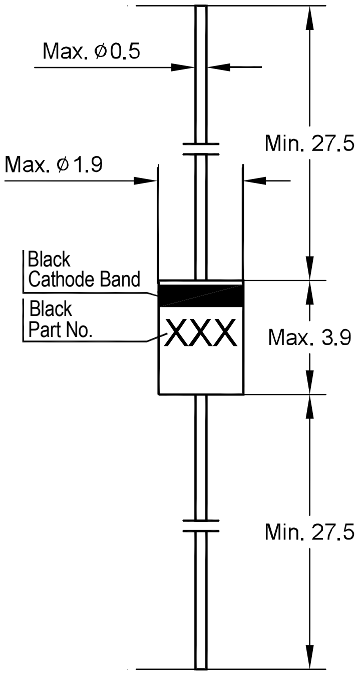
Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Max.	Unit
Forward Current at V_F = 1 V		I_F	4	-	mA
Reverse Current at V_R = 10 V	1N60P 1N60S	I_R	- -	50 100	µA
Junction Capacitance at f = 1 MHz, V = -1 V		C	-	1	pF
Rectification efficiency at Vi = 2 Vrms, R = 5 KΩ, C = 20 pF, f = 40 MHz		η	55	-	%

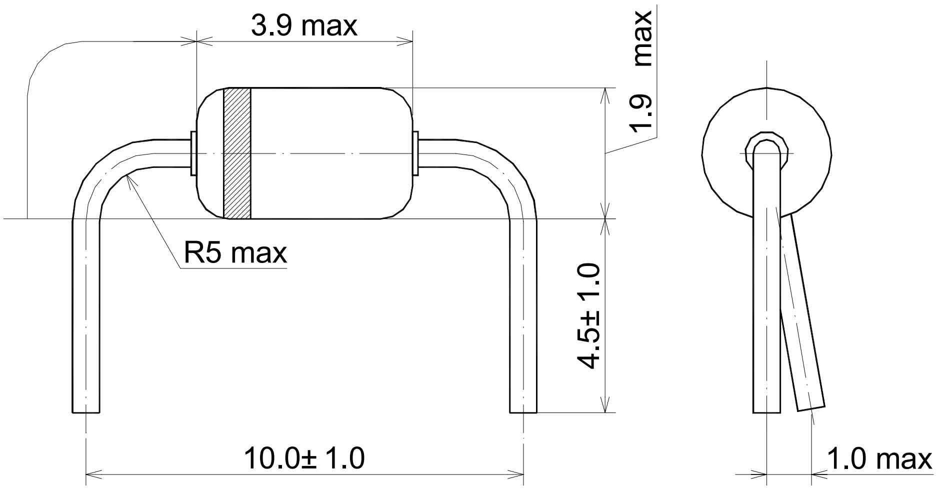


Rectification Efficiency Measurement Circuit

DO- 35 Package Outline Dimensions



Glass Case DO-35
Dimensions in mm



Glass case DO-35-1
Dimensions in mm